



Mechanical Data	Notes
Dice size	Ax=Ay=330um/Bx=By=150um
Wafer size	4" (Gross die:62,800pcs/Good die>59,660pcs)
Chip Thickness	138um±12um
Scribe line width	40um
Top metal	Al/Au/Ag
Back side metal	Al/Au/Ag/Sn

Parameter	Symbol	Conditions	Value	Unit
Reverse stand-off voltage	VRWM		5.0	V
Peak pulse power	PPP	Tp=8/20us	75**	W
Peak pulse current	IPP	Tp=8/20us	5.0*	A
Electrostatic discharge	VESD	IEC61000-4-2 Level 4	± 30(Contact) ±30(Air)	KV
Max.junction temp.	Tj		150	°C

Characteristics TA=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Breakdown voltage	VBR	IT=1mA	5.6		9.4	V
Reverse leakage current	IR	V=± 5V			0.09	uA
Clamping Voltage	VC	IPP=1.0A IPP=5.0A			9.0* 15.0*	V
Diode capacitance	Cj	VR=0V f=1MHZ		10.0	15.0	pf

Notes:

(1)sampling testing:no bad dice inking/guaranteed good die >95%

(2)Testing follow customer

(3) $T_j = T_a + R_{th(j-a)} * (p_f + p_r)$, where $R_{th(j-a)}$ -thermal resistance, P_f -forward power dissipation, P_r -revers power dissipation

(4)**For device testing